

SOT23 NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - NOVEMBER 1995

FEATURES

- * 350 Volt V_{CEO}
- * Gain of 15 at $I_C=100mA$

APPLICATIONS

- * SUITABLE FOR AMPLIFIER AND SWITCHING PRODUCTS

COMPLEMENTARY TYPE - FMMT6520

PARTMARKING DETAIL - 517

ABSOLUTE MAXIMUM RATINGS.

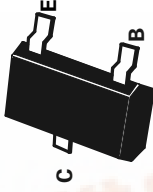
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	350	V
Collector-Emitter Voltage	V_{CEO}	350	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	350		V	$I_C=100\mu A, I_E=0$
	$V_{(BR)CEO}$	350		V	$I_C=1mA, I_B=0^*$
	$V_{(BR)EBO}$	5		V	$I_E=10\mu A, I_C=0$
Cut-Off Currents	I_{CBO}		50	nA	$V_{CB}=250V, I_E=0$
	I_{EBO}		50	nA	$V_{EB}=5V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.3	V	$I_C=10mA, I_B=1mA^*$
			0.35	V	$I_C=20mA, I_B=2mA^*$
			0.5	V	$I_C=30mA, I_B=3mA^*$
			1.0	V	$I_C=50mA, I_B=5mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.80	V	$I_C=10mA, I_B=1mA^*$
			0.85	V	$I_C=20mA, I_B=2mA^*$
			0.90	V	$I_C=30mA, I_B=3mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		2.0	V	$I_C=100mA, V_{CE}=10V^*$
Static Forward Current Transfer Ratio	h_{FE}	20			$I_C=1mA, V_{CE}=10V$
		30			$I_C=10mA, V_{CE}=10V^*$
		30	200		$I_C=30mA, V_{CE}=10V^*$
		20	200		$I_C=50mA, V_{CE}=10V^*$
Output Capacitance	C_{ob0}		6	pF	$V_{CB}=20V, f=1MHz$
	f_T	50		MHz	$I_C=10mA, V_{CE}=20V, f=20MHz$

*Measured under pulsed conditions. Pulse width=300 μ s. Duty cycle \leq 2%

FMMT6517



SOT23

查询FMMT6517供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

